SEARCH REQUEST FORM

Scientific and Technical Information Center

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Requester's Full Name: Robert Kur Art Unit:[765 Phone No Mail Box and Bldg/Room Location:	(P# 3" 10 207 Kesul	is i offinal i formation	2/25/01 345 ER)DISK E-MAIL
f more than one search is submi	tted, please prioritize	searches in order of need.	******
************************************* Please provide a detailed statement of the solude the elected species or structures, ke attility of the invention. Define any terms to known. Please attach a copy of the cover significant to the cover signif	search topic, and describe a eywords, synonyms, acrony that may have a special me- theet, pertinent claims, and	s specifically as possible the subject mat ems, and registry numbers, and combine uning. Give examples or relevant citatio abstract.	with the concept or ns, authors, etc. if
Title of Invention:			
nventors (please provide full names):			
- Paris Fills - Data			
Earliest Priority Filing Date: *For Sequence Searches Only* Please inclu	de all pertinent information (parent, child, divisional, or issued patent ni	imbers) along with the
anneanriate serial number.			
Citagalia sevich pat	ent number 6,0	007,622 12/26/99	
(N	iventors Tomoh	iro Kawase	
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STAFF USE ONLY	Type of Search	Vendors and cost where	applicable
Searcher: Mellecism	NA Sequence (#)	STN	
Searcher Phone #:	AA Sequence (#)		
Searcher Location:	Structure (#)	Questel/Orbit	
Date Searcher Picked Up:	Bibliographic	40.00	
Date Completed: 2/27/0	Litigation	Lexis/NexisSequence Systems	
Searcher Prep & Review Time:	Fulltext Patent Family	WWW/Internet	
Clerical Prep Time:	Other	Other (specify)	
Online Time:	- Juni		

?US6007622/PN

** SS 1: Results 1

Search statement 2

PRT FULL NONSTOP LEGALALL

1/1 PLUSPAT - (C) QUESTEL-ORBIT

PN - US6007622 A 19991228 [US6007622]

TI - (A) Method of preparing group III-V compound semiconductor crystal

PA - (A) SUMITOMO ELECTRIC INDUSTRIES (JP)

IN - (A) KAWASE TOMOHIRO (JP); TATSUMI MASAMI (JP)
AP - US84312497 19970425 [1997US-0843124]
PR - JP10700996 19960426 [1996JP-0107009]

IC - (A) C30B-011/04

EC - C30B-011/00 C30B-029:40

- C30B-011/00 C30B-029:42

PCL - ORIGINAL (O) : 117082000; CROSS-REFERENCE (X) : 117004000 117006000 117007000 117083000 117953000

DT - Corresponding document

CT - US4999082; US5131975; US5515810; EP0529963; JP60-210599; JP01037833; JP64-79087; JP02034597; JP2-74597; JP3-252399

- Journal of Japanese Association of Crystal Growth, Y. Okabe et al. Undoped Semi-Insulating GaAs Single Crystals Grown by VGF Method, vol. 18, 1991, pp. 88-95.

"Low dislocation density and low residual strain semi insulating GaAs grown by vertical boat method". Kawase, T. (Apr. 1996).

STG - (A) United States patent

AB - A method is provided for preparing, with high reproducibility, a carbon-doped group III-V compound semiconductor crystal having favorable electrical characteristics and having impurities removed therefrom, and in which the amount of doped carbon can be adjusted easily during crystal growth. This method includes the steps of: filling a crucible with compound raw material, solid carbon, and boron oxide; sealing the filled crucible gas impermeable material; heating and melting the compound raw material under the sealed state in the airtight vessel; and solidifying the melted compound raw material to grow a carbon-doped compound semiconductor crystal.

1/1 LGST - (C) LEGSTAT

PN - US 6007622 [US6007622]

AP - US 843124/97 19970425 [1997US-0843124]

DT - US-P

ACT - 19970425 US/AE-A

APPLICATION DATA (PATENT)

{US 843124/97 19970425 [1997US-0843124]}

- 19991228 US/A

PATENT

- 20010717 US/RF

REISSUE APPLICATION FILED

20010403

- 20011127 US/CC CERTIFICATE OF CORRECTION

UP - 2001-51

1/1 CRXX - (C) CLAIMS/RRX

PN - 6,007,622 A 19991228 [US6007622] PA - Sumitomo Electric Industries Ltd JP

ACT - 20010403 REISSUE REQUESTED ISSUE DATE OF O.G.: 20010717 FEISSUE REQUEST NUMBER: 09/824965

EXAMINATION GROUP RESPONSIBLE FOR REISSUEPROCESS: 1765

Reissue Patent Number:

- 20011218 CERTIFICATE OF CORRECTION

1/2 PAST - (C) PAST

AN - 200151-000601

PN - 6007622 A [US6007622]

og - 2001-12-18

ACT - CERTIFICATE OF COFRECTION

2/2 PAST - (C) PAST

AN - 200129-001177

PN - 6007622 A [US6007622]

og - 2001-07-17

ACT - REISSUE APPLICATION FILED

Search statement 2

?FILE INPADOC

PLUSPAT - Time in minutes : 0,92

The cost estimation below is based on Questel's

standard price list

Estimated cost: 2.02 USD

Records displayed and billed : 1

Estimated cost : 1.10 USD Cost estimated for the last database search : 3.12 USD

3.70 USD Estimated total session cost

- Time in minutes : (1,1)7

The cost estimation below is based on Questel's

standard price list

Estimated cost: 0.07 USD

Records displayed and billed : 1

Estimated cost : 0.57 USD Cost estimated for the last database search : 0.64 USD

: 4.34 USD Estimated total session cost

- Time in minutes: 0,09 CRXX

The cost estimation below is based on Questel's standard price list Estimated cost: 0.13 USD Records displayed and billed : 1 Estimated cost : 5.00 USD Cost estimated for the last database search : 5.13 USD Estimated total session cost : 9.47 USD Estimated total session cost - Time in minutes: 0,06 The cost estimation below is based on Questel's standard price list 0.11 USD Estimated cost : Records displayed and billed : 2 Estimated cost: 11.22 USD Cost estimated for the last database search: 11.33 USD Estimated total session cost The cost estimation below is based on Questel's standard price list Estimated cost: 0.01 USD Cost estimated for the last database search: 0.01 USD : 20.81 USD Estimated total session cost Selected file: INPADOC You are now connected to INPADOC Covers 1968/1973 thru weekly updates (2002-07) For information on content, .. INFO INPD. Search statement 1 ?FAM US6007622/PN 1 Patent Groups ** SS 1: Results 4 Search statement 2 ?FAMSTATE NONSTOP PN - EP 803593 A1 19971029 [EP-803593]
TI - METHOD OF PREPARING GROUP III-V COMPOUND SEMICONDUCTOR CRYSTAL
LA - ENG
IN - KAWASA TOMOHIRO [JP]; TATSUMI MASAMI [JP] PA - SUMITOMO ELECTRIC INDUSTRIES [JP] AF - EP 97106815/97-A 19970424 [1997EP-0106815] PR - JP 107009/96-A 19960426 [1996JP-0107009] IC - C30B-011/00; C30B-029/40; C30B-029/42 DS - DE* FR* GB* 1/1 LEGALI - (C) LEGSTAT PN - EP 803593 [EP-803593] AP - EP 97106815/97 19970424 [1997EP-0106815] DT - EP-P

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Robert Kunenunel
  ACTE- 19970424 EP/AE-A
        EP-APPLICATION
        {EP 97106815/97 19970424 [1997EP-0106815]}
        DESIGNATED CONTPACTING STATES IN AN APPLICATION WITH SEARCH REPORT:
       - 19971029 EP/AK-A1 [+]
        DE FR GB
      - 19971029 EP/A1 [+]
        PUBLICATION OF APPLICATION WITH SEARCH REPORT
       - 19971217 EP/17P [+]
        REQUEST FOR EXAMINATION FILED
         971017
       - 19991208 EP/17Q [+]
         FIRST EXAMINATION REPORT
         19991026
       - 20000112 EP/FIN1
         HAWASE, TOMOHIRO, SUMITOMO ELECTRIC IND., LTD. * TATSUMI, MASAMI,
         SUMITOMO ELECTRIC IND., LTD.
   UP - 2000-02
   2/4 INPADOC - (C) INFADOC
   PN - JP 3201305 B2 20010820 [JP3201305]
   AP - JP 106115/97-A 19970423 [1997JP-0106115]
   PR - JP 106115/97-A 19970423 [1997JP-0106115]
- JP 107009/96-A 19960426 [1996JP-0107009]
   IC - C30B-029/40; C30B-011/00; C30B-029/42
    3/4 INFADOC - (C) INPADOC
    PN - JP 10036197 A2 19930210 [JP10036197]
       - PRODUCTION OF III-V COMPOUND SEMICONDUCTOR CRYSTAL
    IN - KAWASE TOMOHIRO; TATSUMI MASAMI
    PA - SUMITOMO ELECTRIC INDUSTRIES
    AP - JP 106115/97-A 19970423 [1997JF-0106115]
PR - JP 106115/97-A 19970423 [1997JF-0106115]
- JP 107009/96-A 19960426 [1996JF-0107009]
    IC - C30B-029/40; C30B-011/00; C30B-029/42
     4/4 INPADOC - (C) INPADOC
    PN - US 6607622 A 19991223 [US6007622]
    TI - METHOD OF PREPARING GROUP III-V COMPOUND SEMICONDUCTOR CRYSTAL
     IN - KAWASE TOMOHIFO [JP]; TATSUMI MASAMI [JP]
     PA - SUMITOMO ELECTRIC INDUSTRIES [JP]
     AP - US 843124/97-A 19970425 [1997US-0843124]
     PR - JP 107009/96-A 19960426 [1996JP-0107009]
     IC - C30B-011/04
     1/1 LEGALI - (C) LEGSTAT
     PN - US 6007622 [US6007622]
     AP - US 843124/97 19970425 [1997US-0843124]
     DT - US-P
     ACTE- 19970425 US/AE-A
            APPLICATION DATA (PATENT)
            {US 843124/97 19970425 [1997US-0843124]}
          - 19991218 US/A
            PATENT
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- 20010717 US/RF REISSUE APPLICATION FILED 20010403

- 20011127 US/CC CERTIFICATE OF CORRECTION

UP - 2001-51

Search statement 2

DATE: FEBRUARY 25, 2002 LIBRARY: PATENT FILE: ALL

Your search request is: PATNO IS 6007622

Number of PATENTS found with your search request through: LEVEL 1... 1

Your search request has found 1 PATENT through Level 1. To DISPLAY this PATENT press either the KWIC, FULL, CITE or SEGMTS key. To MODIFY your search request, press the M key (for MODFY) and then the ENTER

For further explanation, press the H key (for HELP) and then the ENTER key.

LEVEL 1 - 1 PATENT

1. 6,007,622, Dec. 28, 1999, Method of preparing group III-V compound semiconductor crystal, Kawase, Tomohiro, Hyogo, Japan Tatsumi, Masami, Hyogo, Japan, Sumitomo Electric Industries, Ltd., Osaka, Japan (03)

CORE TERMS: carbon, crystal, compound, boron, oxide, semiconductor, raw material, preparing, crucible, carbon-doped...

LEVEL 1 - 1 OF 1 PATENT

6,007,622

<=2> GET 1st DRAWING SHEET OF 7

Dec. 28, 1999

Method of preparing group III-V compound semiconductor crystal

REISSUE: Reissue Application filed Apr. 3, 2001 (O.G. Jul. 17, 2001) Ex. Gp.: 1765; Re. S.N. 09/824,965

CERTCORR: Nov. 27, 2001 a Certificate of Correction was issued for this patent (O.G. Dec. 18, 2001)

CORE TERMS: carbon, crystal, compound, boron, oxide, semiconductor, raw material, preparing, crucible, carbon-doped...

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To enter a new search request, type it and press the ENTER key.

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For further explanation, press the H key (for HELP) and then the ENTER key.